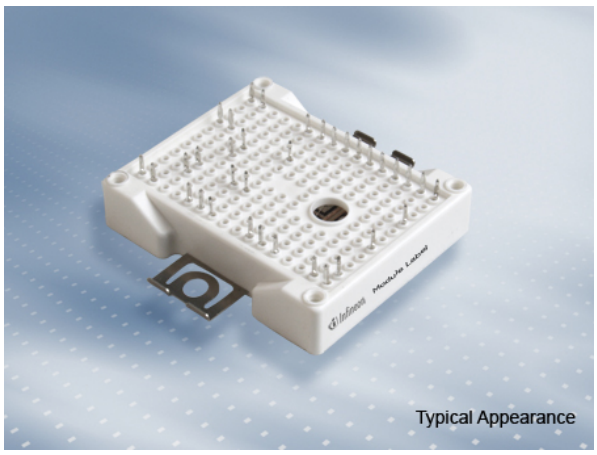
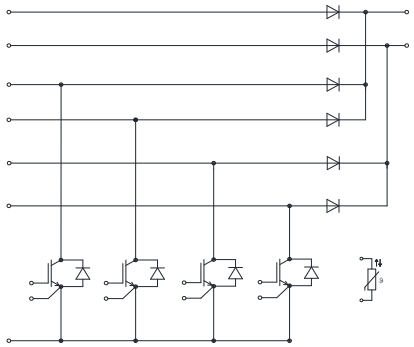
技术信息 / Technical Information

IGBT-模块
IGBT-modules

DF160R12W2H3_B11

初步数据 / Preliminary Data





V_{CES} = 1200V
$I_{C\ nom}$ = 160A / I_{CRM} = 320A

典型应用
- 太阳能应用
- UPS系统

Typical Applications
- Solar Applications
- UPS Systems

电气特性
- 高速IGBT H3
- 低开关损耗

Electrical Features
- High Speed IGBT H3
- Low Switching Losses

机械特性
- 低热阻的三氧化二铝（ Al_2O_3 衬底
- 集成NTC温度传感器
- 紧凑型设计
- PressFIT 压接技术

Mechanical Features
- Al_2O_3 Substrate with Low Thermal Resistance
- Integrated NTC temperature sensor
- Compact design
- PressFIT Contact Technology

Module Label Code

Barcode Code 128

Sample
00000123456000000000000

DMX - Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: CM	date of publication: 2013-11-11	
approved by: MB	revision: 2.0	UL approved (E83335)

初步数据
Preliminary Data

旁路二极管 / Bypass-Diode

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1200	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	T_C = 80°C	I_{FRMSM}	50	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	T_C = 80°C	I_{RMSM}	60	A
正向浪涌电流 Surge forward current	t_p = 10 ms, T_{vj} = 25°C t_p = 10 ms, T_{vj} = 150°C	I_{FSM}	450 360	A A
I2t-值 I²t - value	t_p = 10 ms, T_{vj} = 25°C t_p = 10 ms, T_{vj} = 150°C	I²t	1000 650	A²s A²s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	T_{vj} = 150°C, I_F = 30 A	V_F		0,95		V
反向电流 Reverse current	T_{vj} = 150°C, V_R = 1200 V	I_R		0,10		mA
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	R_{thJC}		0,80	1,05	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)	R_{thCH}		0,80		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\,op}$				°C

反极性保护二极管A / Inverse-polarity protection diode A

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1200	V
最大正向均方根电流(每芯片) Maximum RMS forward current per chip	T_C = 80°C	I_{FRMSM}	30	A
最大整流器输出均方根电流 Maximum RMS current at rectifier output	T_C = 80°C	I_{RMSM}	60	A
正向浪涌电流 Surge forward current	t_p = 10 ms, T_{vj} = 25°C t_p = 10 ms, T_{vj} = 150°C	I_{FSM}	290 245	A A
I2t-值 I²t - value	t_p = 10 ms, T_{vj} = 25°C t_p = 10 ms, T_{vj} = 150°C	I²t	420 300	A²s A²s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	T_{vj} = 150°C, I_F = 20 A	V_F		1,00		V
反向电流 Reverse current	T_{vj} = 150°C, V_R = 1200 V	I_R		0,10		mA
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	R_{thJC}		1,20	1,35	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)	R_{thCH}		1,15		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\,op}$				°C

prepared by: CM	date of publication: 2013-11-11
approved by: MB	revision: 2.0

初步数据
Preliminary Data

IGBT, 斩波器 / IGBT-Chopper

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1200	V
集电极电流 Implemented collector current		I_{CN}	40	A
连续集电极直流电流 Continuous DC collector current	T_C = 100°C, $T_{vj\,max}$ = 175°C T_C = 25°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$ I_C	20 50	A A
集电极重复峰值电流 Repetitive peak collector current	t_P = 1 ms	I_{CRM}	80	A
总功率损耗 Total power dissipation	T_C = 25°C, $T_{vj\,max}$ = 175°C	P_{tot}	190	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	I_C = 20 A, V_{GE} = 15 V, T_{vj} = 25°C I_C = 20 A, V_{GE} = 15 V, T_{vj} = 125°C I_C = 20 A, V_{GE} = 15 V, T_{vj} = 150°C	$V_{CE\,sat}$		1,55 1,70 1,75	1,70	V V V
栅极阈值电压 Gate threshold voltage	I_C = 1,00 mA, V_{CE} = V_{GE}, T_{vj} = 25°C	V_{GEth}	5,0	5,8	6,5	V
栅极电荷 Gate charge	V_{GE} = -15 V ... +15 V	Q_G		0,32		µC
内部栅极电阻 Internal gate resistor	T_{vj} = 25°C	R_{Gint}		0,0		Ω
输入电容 Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V	C_{ies}		2,35		nF
反向传输电容 Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V	C_{res}		0,13		nF
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE} = 1200 V, V_{GE} = 0 V, T_{vj} = 25°C	I_{CES}			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C	I_{GES}			100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	I_C = 20 A, V_{CE} = 600 V, T_{vj} = 25°C V_{GE} = ±15 V, T_{vj} = 125°C R_{Gon} = 12 Ω, T_{vj} = 150°C	$t_{d\,on}$		0,035 0,035 0,035		µs µs µs
上升时间(电感负载) Rise time, inductive load	I_C = 20 A, V_{CE} = 600 V, T_{vj} = 25°C V_{GE} = ±15 V, T_{vj} = 125°C R_{Gon} = 12 Ω, T_{vj} = 150°C	t_r		0,01 0,012 0,014		µs µs µs
关断延迟时间(电感负载) Turn-off delay time, inductive load	I_C = 20 A, V_{CE} = 600 V, T_{vj} = 25°C V_{GE} = ±15 V, T_{vj} = 125°C R_{Goff} = 12 Ω, T_{vj} = 150°C	$t_{d\,off}$		0,25 0,32 0,35		µs µs µs
下降时间(电感负载) Fall time, inductive load	I_C = 20 A, V_{CE} = 600 V, T_{vj} = 25°C V_{GE} = ±15 V, T_{vj} = 125°C R_{Goff} = 12 Ω, T_{vj} = 150°C	t_f		0,016 0,023 0,025		µs µs µs
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	I_C = 20 A, V_{CE} = 600 V, L_S = 30 nH, T_{vj} = 25°C V_{GE} = ±15 V, di/dt = 1800 A/µs (T_{vj} = 150°C), T_{vj} = 125°C R_{Gon} = 12 Ω, T_{vj} = 150°C	E_{on}		0,90 1,55 1,75		mJ mJ mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	I_C = 20 A, V_{CE} = 600 V, L_S = 30 nH, T_{vj} = 25°C V_{GE} = ±15 V, du/dt = 3200 V/µs (T_{vj} = 150°C), T_{vj} = 125°C R_{Goff} = 12 Ω, T_{vj} = 150°C	E_{off}		0,80 1,20 1,40		mJ mJ mJ
短路数据 SC data	V_{GE} ≤ 15 V, V_{CC} = 800 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt, t_P ≤ 10 µs, T_{vj} = 150°C	I_{SC}		130		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT	R_{thJC}		0,55	0,65	K/W

初步数据
Preliminary Data

外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)	R_{thCH}		0,55		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40		150	°C

Diode-斩波器 / Diode-Chopper

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}		1200		V
连续正向直流电流 Continuous DC forward current		I_F		20		A
正向重复峰值电流 Repetitive peak forward current	t_P = 1 ms	I_{FRM}		70		A
I2t-值 I²t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C	I²t		360		A²s

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	I_F = 20 A, V_{GE} = 0 V I_F = 20 A, V_{GE} = 0 V I_F = 20 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,70 1,35 1,30	2,00	V V V
反向恢复峰值电流 Peak reverse recovery current	I_F = 20 A, - di_F/dt = 1800 A/µs (T_{vj}=150°C) V_R = 600 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		36,0 53,0 58,0		A A A
恢复电荷 Recovered charge	I_F = 20 A, - di_F/dt = 1800 A/µs (T_{vj}=150°C) V_R = 600 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		1,65 3,90 5,00		µC µC µC
反向恢复损耗（每脉冲） Reverse recovery energy	I_F = 20 A, - di_F/dt = 1800 A/µs (T_{vj}=150°C) V_R = 600 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		0,86 1,90 2,40		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,70	0,75	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)		R_{thCH}		0,70		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40		150	°C

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	T_C = 25°C	R_{25}		5,00		kΩ
R100 偏差 Deviation of R100	T_C = 100°C, R_{100} = 493 Ω	ΔR/R	-5		5	%
耗散功率 Power dissipation	T_C = 25°C	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\ K))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\ K))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\ K))]$	$B_{25/100}$		3433		K

根据应用手册标定
Specification according to the valid application note.

初步数据
Preliminary Data

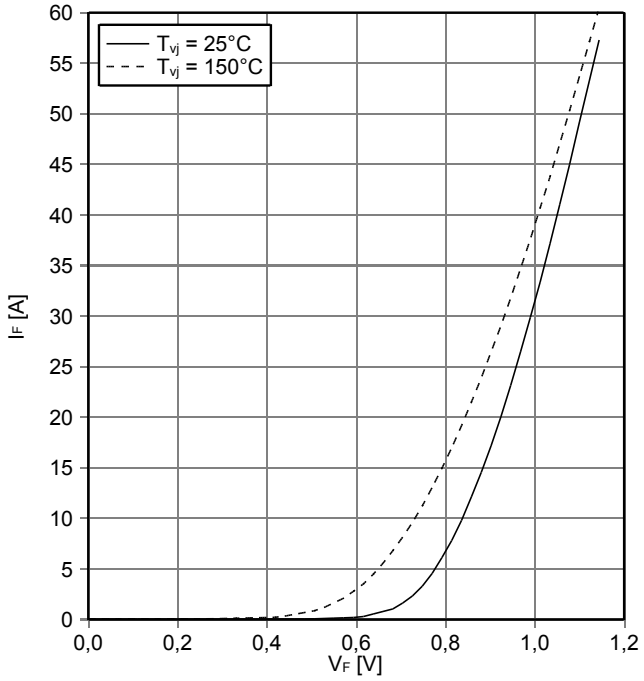
模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}		2,5		kV
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)			Al_2O_3		
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal			11,5 6,3		mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal			10,0 5,0		mm
相对电痕指数 Comperative tracking index		CTI		> 200		
			min.	typ.	max.	
杂散电感,模块 Stray inductance module		L_{sCE}		20		nH
储存温度 Storage temperature		T_{stg}	-40		125	°C
Anpresskraft für mech. Bef. pro Feder mountig force per clamp		F	40	-	80	N
重量 Weight		G		36		g

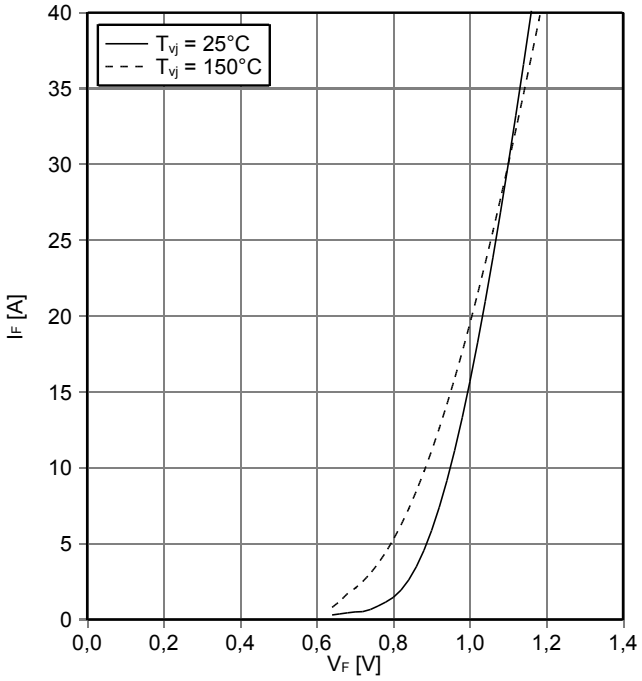
Der Strom im Dauerbetrieb ist auf 25A effektiv pro Anschlusspin begrenzt
The current under continuous operation is limited to 25A rms per connector pin

初步数据
Preliminary Data

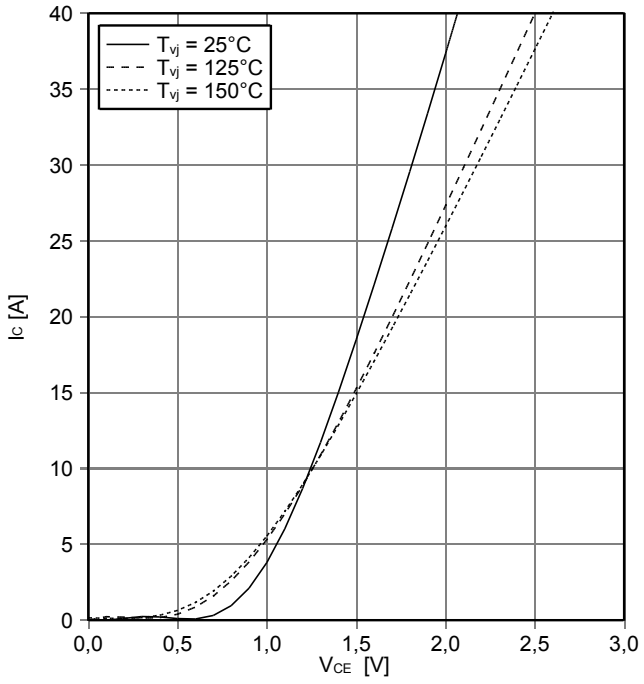
正向偏压特性 旁路二极管 (典型)
forward characteristic of Bypass-Diode (typical)
$I_F = f(V_F)$



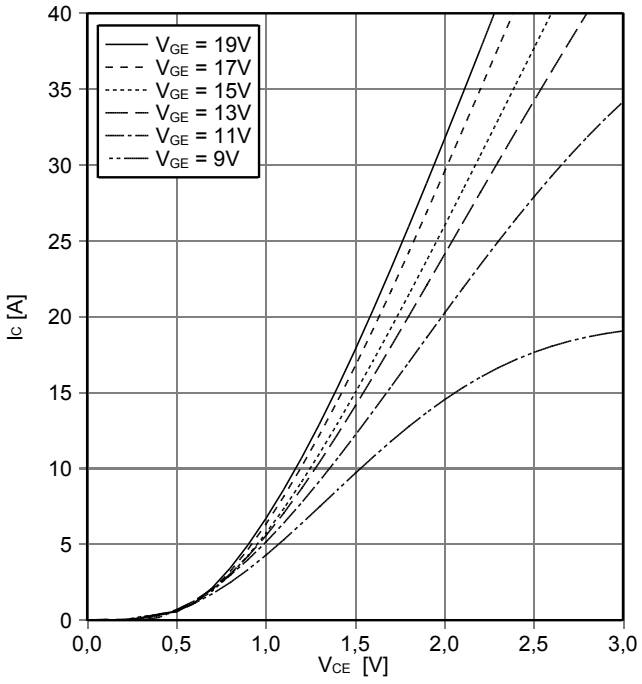
正向偏压特性 反极性保护二极管A (典型)
forward characteristic of Inverse-polarity protection diode A (typical)
$I_F = f(V_F)$



输出特性 IGBT, 斩波器 (典型)
output characteristic IGBT-Chopper (typical)
$I_C = f(V_{CE})$
V_{GE} = 15 V



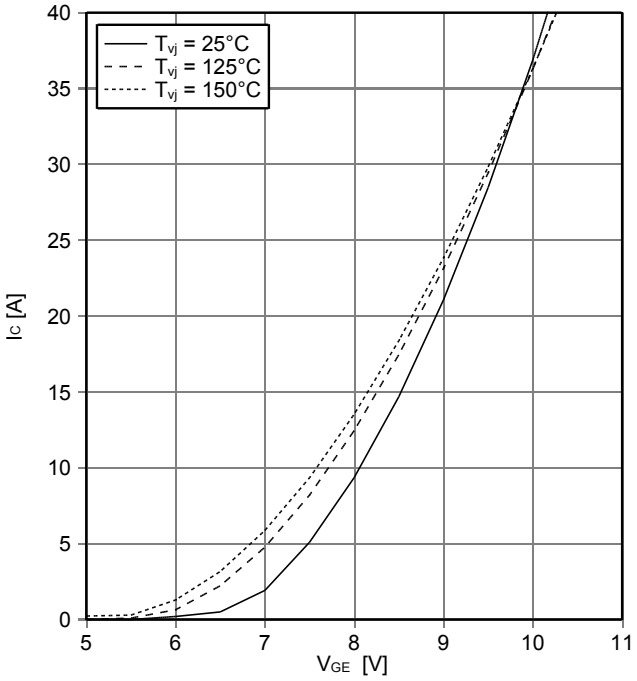
输出特性 IGBT, 斩波器 (典型)
output characteristic IGBT-Chopper (typical)
$I_C = f(V_{CE})$
T_{vj} = 150°C



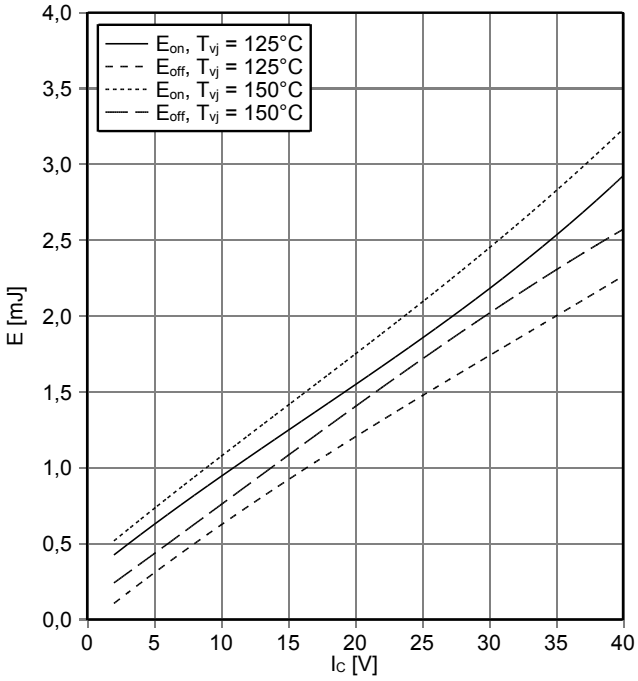
prepared by: CM	date of publication: 2013-11-11
approved by: MB	revision: 2.0

初步数据
Preliminary Data

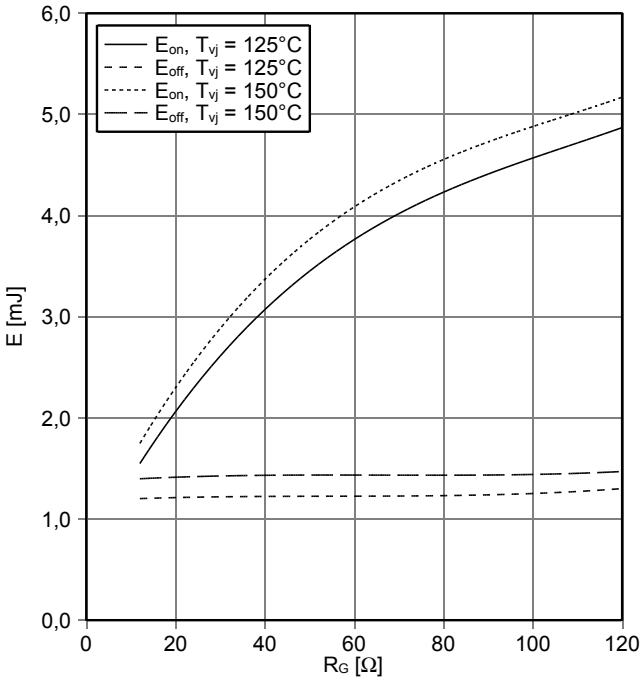
传输特性 IGBT, 斩波器 (典型)
transfer characteristic IGBT-Chopper (typical)
$I_C = f(V_{GE})$
V_{CE} = 20 V



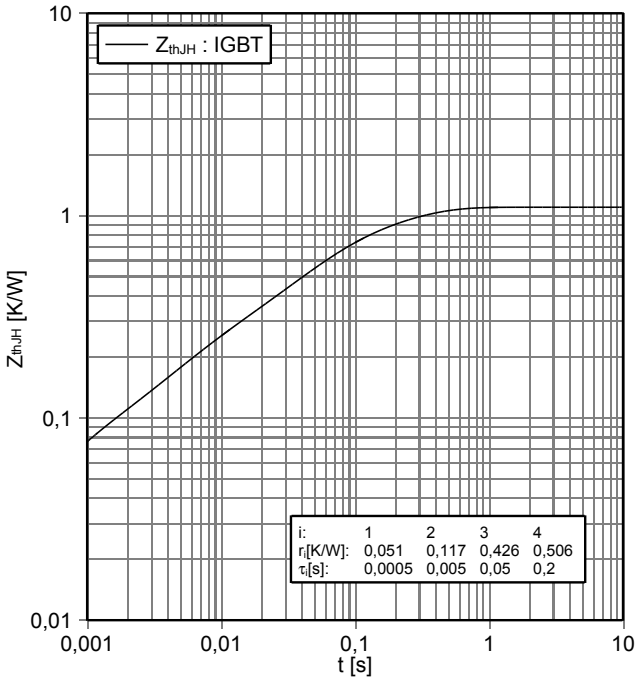
开关损耗 IGBT, 斩波器 (典型)
switching losses IGBT-Chopper (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
V_{GE} = ±15 V, R_{Gon} = 12 Ω, R_{Goff} = 12 Ω, V_{CE} = 600 V



开关损耗 IGBT, 斩波器 (典型)
switching losses IGBT-Chopper (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
V_{GE} = ±15 V, I_C = 20 A, V_{CE} = 600 V



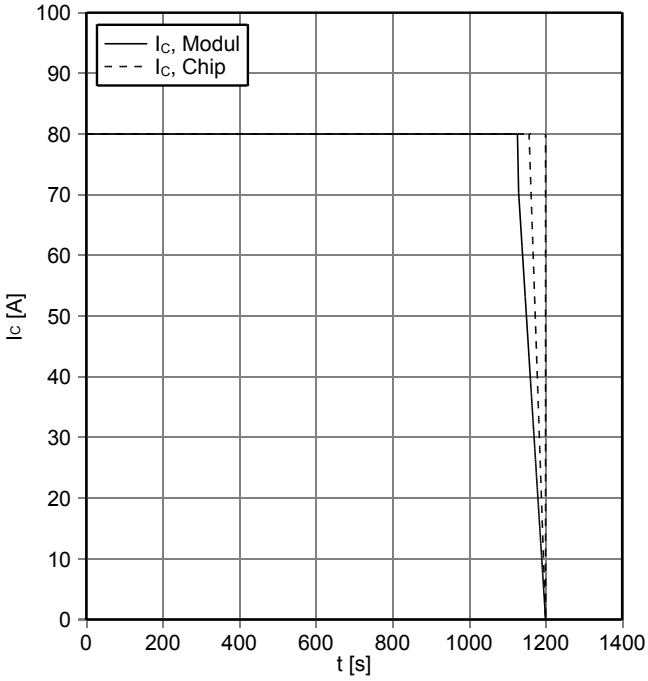
瞬态热阻抗 IGBT, 斩波器
transient thermal impedance IGBT-Chopper
$Z_{thJH} = f(t)$



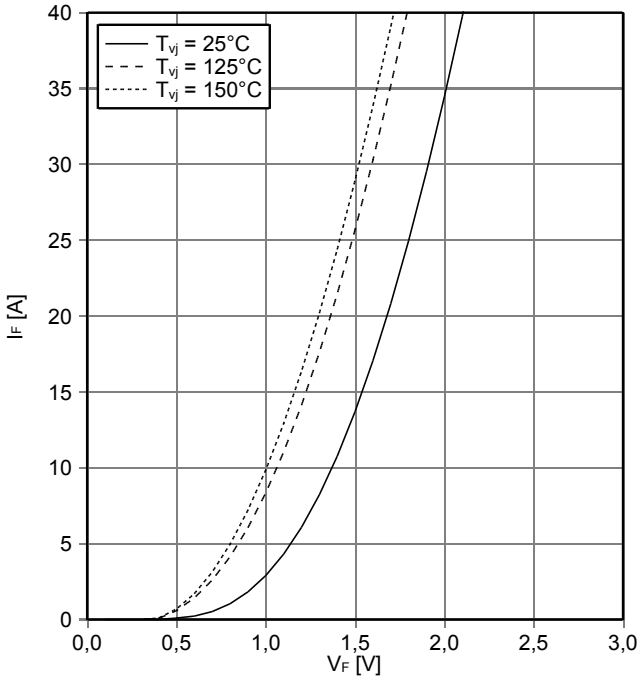
prepared by: CM	date of publication: 2013-11-11
approved by: MB	revision: 2.0

初步数据
Preliminary Data

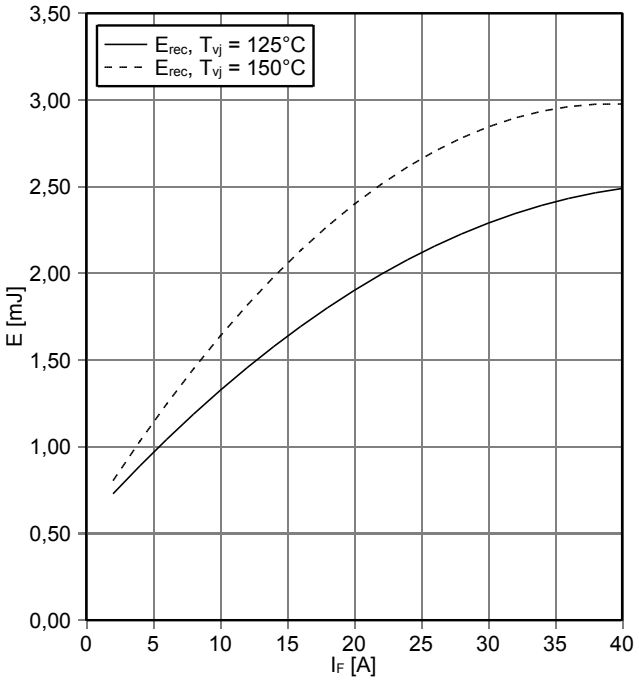
反偏安全工作区 IGBT, 斩波器 （RBSOA）
reverse bias safe operating area IGBT-Chopper (RBSOA)
$I_C = f(V_{CE})$
$V_{GE} = \pm 15$ V, $R_{Goff} = 12\ \Omega$, $T_{vj} = 150°C$



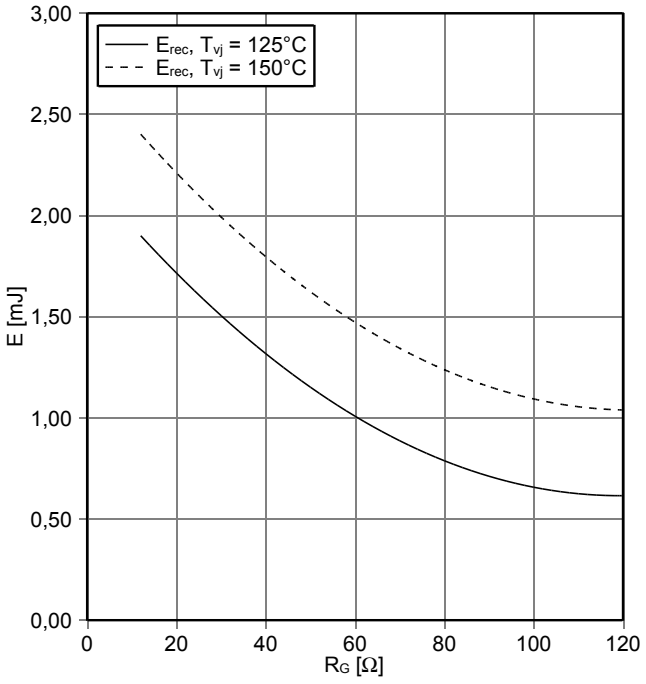
正向偏压特性 Diode-斩波器 （典型）
forward characteristic of Diode-Chopper (typical)
$I_F = f(V_F)$



开关损耗 Diode-斩波器 （典型）
switching losses Diode-Chopper (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 12\ \Omega$, $V_{CE} = 600$ V



开关损耗 Diode-斩波器 （典型）
switching losses Diode-Chopper (typical)
$E_{rec} = f(R_G)$
$I_F = 20$ A, $V_{CE} = 600$ V



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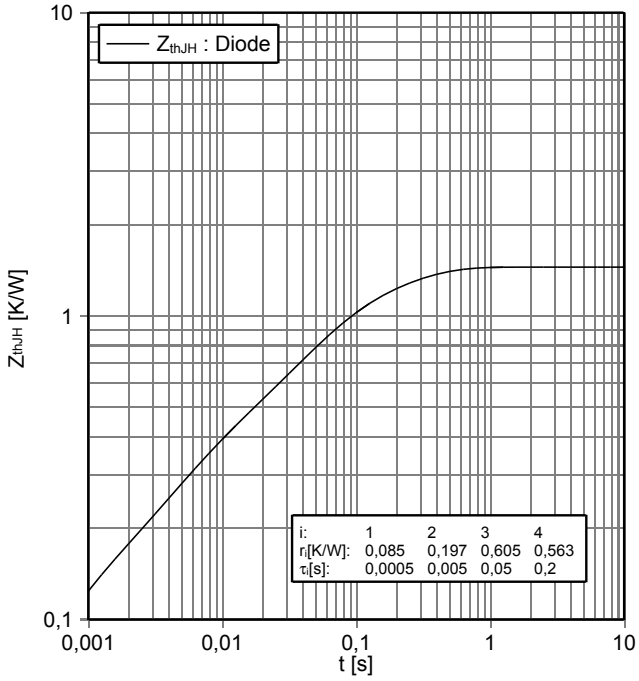
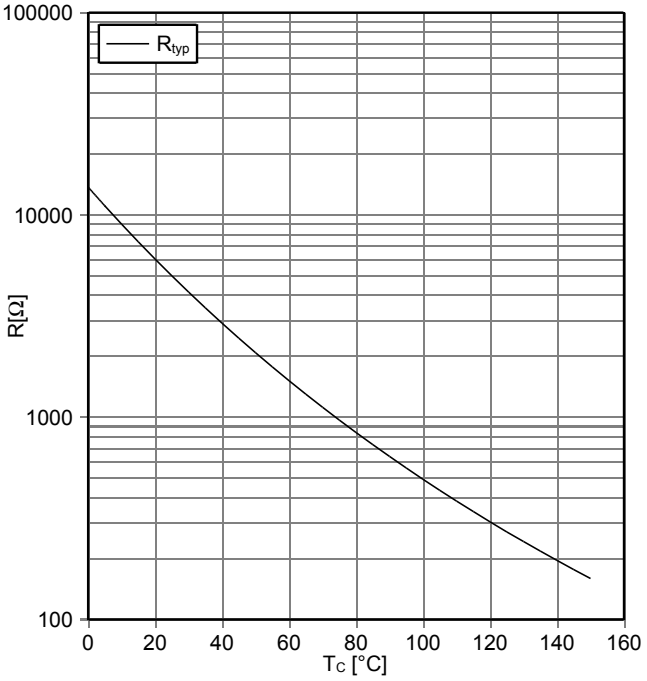
初步数据
Preliminary Data

瞬态热阻抗 Diode-斩波器
transient thermal impedance Diode-Chopper
$Z_{thJH} = f(t)$



负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)
$R = f(T)$



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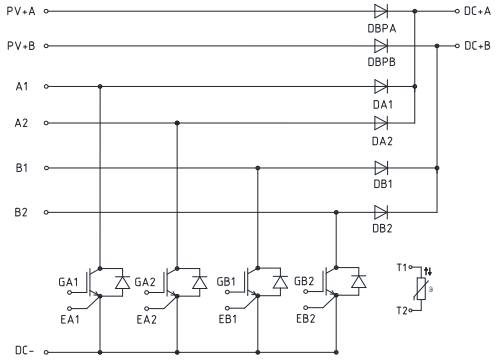
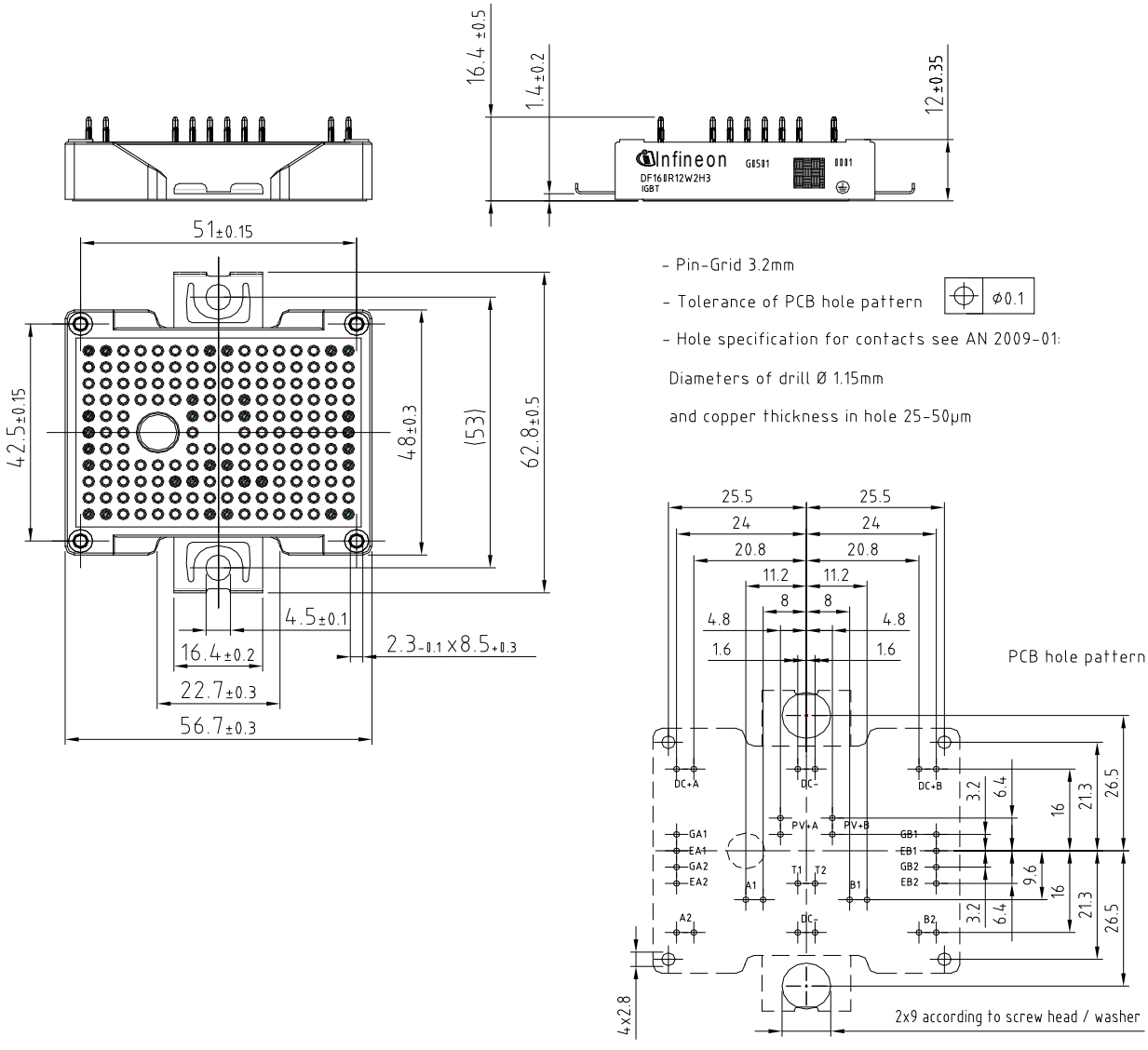
初步数据
Preliminary Data

接线图 / circuit_diagram_headline



封装尺寸 / package outlines



prepared by: CM	date of publication: 2013-11-11
approved by: MB	revision: 2.0

初步数据
Preliminary Data

使用条件和条款

使用条件和条款
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approved by: MB	revision: 2.0

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